

PMBFJ111; PMBFJ112; PMBFJ113

N-channel junction FETs

Rev. 4 — 20 September 2011

Product data sheet

1. Product profile

1.1 General description

Symmetrical N-channel junction FETs in a SOT23 package.

1.2 Features and benefits

- High-speed switching
- Interchangeability of drain and source connections
- Low R_{DSon} at zero gate voltage (< 30 Ω for PMBFJ111).

1.3 Applications

- Analog switches
- Choppers
- Commutators
- Multiplexers
- Thin and thick film hybrids.

2. Pinning information

Table 1. Pinning

Pin	Description ^[1]	Simplified outline	Symbol
1	drain		
2	source		
3	gate	1 2	3 → 1 2 sym053

^[1] Drain and source are interchangeable.



3. Ordering information

Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
PMBFJ111	-	plastic surface mounted package; 3 leads	SOT23		
PMBFJ112					
PMBFJ113					

4. Marking

Table 3. Marking

3	
Type number	Marking code ^[1]
PMBFJ111	41*
PMBFJ112	42*
PMBFJ113	47*

^{[1] * =} p: Made in Hong Kong

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	±40	V
V_{GSO}	gate-source voltage		-	-40	V
V_{GDO}	gate-drain voltage		-	-40	V
I _G	forward gate current (DC)		-	50	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1] -	300	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C

^[1] Mounted on a ceramic substrate, 8 mm \times 10 mm \times 0.7 mm.

6. Thermal characteristics

Table 5. Thermal characteristics

 $T_j = P\left(R_{th(j-t)} + R_{th(t-s)} + R_{th(s-a)}\right) + T_{amb}.$

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u> 430	K/W
	thermal resistance from junction to ambient		^[2] 500	K/W

^[1] Mounted on a ceramic substrate, 8 mm \times 10 mm \times 0.7 mm.

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^{* =} t: Made in Malaysia

^{* =} W: Made in China

^[2] Mounted on printed circuit board.

7. Static characteristics

Table 6. Static characteristics

 $T_i = 25 \, ^{\circ}C$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate-source leakage current	$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	-1	nΑ
I _{DSS}	drain-source leakage current					
	PMBFJ111	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	20	-	-	mΑ
	PMBFJ112	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	5	-	-	mΑ
	PMBFJ113	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	2	-	-	mΑ
$V_{(BR)GSS}$	gate-source breakdown voltage	$I_G = -1 \mu A; V_{DS} = 0 V$	-40	-	-	V
V_{GSoff}	gate-source cut-off voltage					
	PMBFJ111	$I_D = 1 \mu A; V_{DS} = 5 V$	-10	-	-3	V
	PMBFJ112	$I_D = 1 \mu A; V_{DS} = 5 V$	-5	-	-1	V
	PMBFJ113	$I_D = 1 \mu A; V_{DS} = 5 V$	-3	-	-0.5	V
R _{DSon}	drain-source on-state resistance					
	PMBFJ111	$V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	-	-	30	Ω
	PMBFJ112	$V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	-	-	50	Ω
	PMBFJ113	$V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	-	-	100	Ω

8. Dynamic characteristics

Table 7. Dynamic characteristics

	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 0 V; V_{GS} = -10 V; f = 1 MHz$	-	6	-	pF
		$V_{DS} = 0 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	22	28	pF
C _{rss}	feedback capacitance		-	3	-	pF
Switching	g times; see Figure 2					
t _r	rise time		[1] -	6	-	ns
t _{on}	turn-on time		[1] -	13	-	ns
t _f	fall time		[1] -	15	-	ns
t _{off}	turn-off time		[1] -	35	-	ns

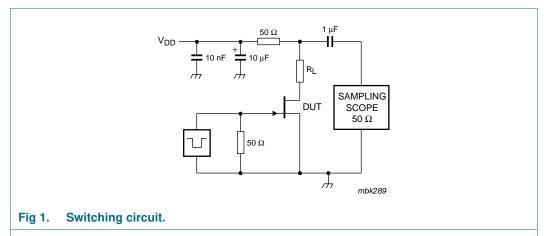
[1] Test conditions for switching times are as follows:

 $V_{DD} = 10 \text{ V}, V_{GS} = 0 \text{ V to } V_{GSoff} \text{ (all types)};$

 $V_{GSoff} = -12 \text{ V}, \text{ R}_{L} = 750 \Omega \text{ (PMBFJ111)};$

 V_{GSoff} = -7 V, R_L = 1550 Ω (PMBFJ112);

 $\mbox{V}_{\mbox{GSoff}} = -5$ V, $\mbox{R}_{\mbox{L}} = 3150~\Omega$ (PMBFJ113).



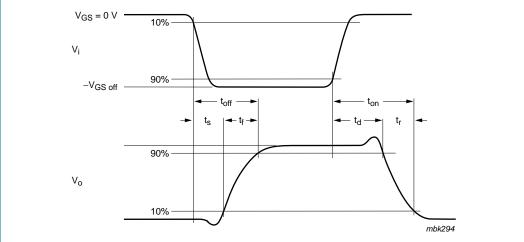


Fig 2. Input and output waveforms.

9. Package outline

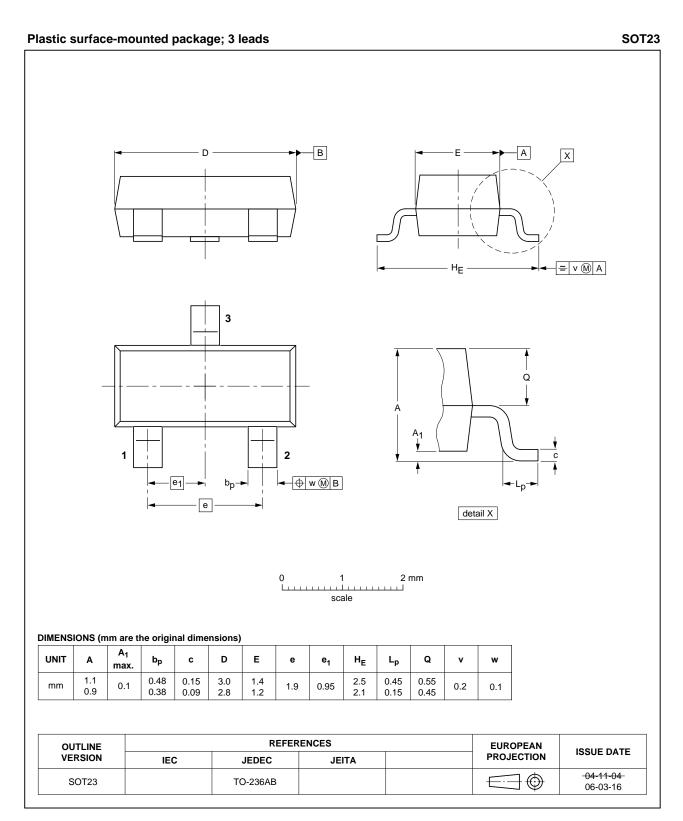


Fig 3. Package outline.

10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBFJ111_112_113 v.4	20110920	Product data sheet	-	PMBFJ111_112_113 v.3
Modifications:	guidelines o • Legal texts	of NXP Semiconductors.	ne new company r	comply with the new identity name where appropriate. atest version.
PMBFJ111_112_113 v.3 (9397 750 13402)	20040804	Product data sheet	-	PMBFJ111_112_113_CNV v.2
PMBFJ111_112_113_CNV v.2	19971201	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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